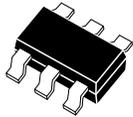


**CMXD4448**  
**SUPER-MINI**  
**TRIPLE ISOLATED**  
**SURFACE MOUNT**  
**HIGH SPEED**  
**SWITCHING DIODE**



**SOT-26 CASE**

# Central<sup>TM</sup>

**Semiconductor Corp.**

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CMXD4448 type contains three (3) Isolated High Speed Silicon Switching Diodes, manufactured by the epitaxial planar process, epoxy molded in a super-mini surface mount package, designed for applications requiring high speed switching applications. Marking code is X48.

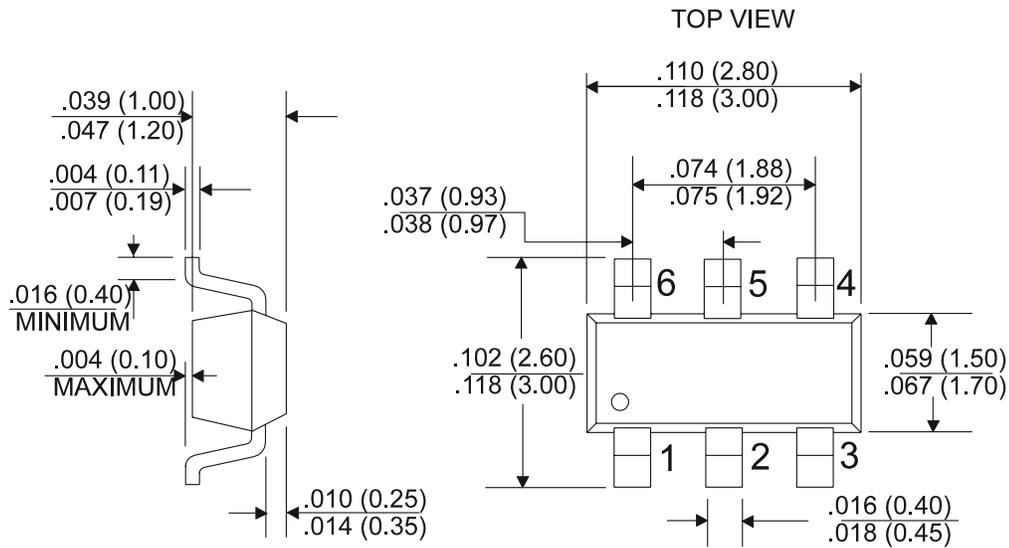
**MAXIMUM RATINGS** ( $T_A=25^\circ\text{C}$ )

	<b>SYMBOL</b>		<b>UNITS</b>
Continuous Reverse Voltage	$V_R$	75	V
Peak Repetitive Reverse Voltage	$V_{RRM}$	100	V
Continuous Forward Current	$I_F$	250	mA
Peak Repetitive Forward Current	$I_{FRM}$	250	mA
Forward Surge Current, $t_p=1 \mu\text{sec.}$	$I_{FSM}$	4000	mA
Forward Surge Current, $t_p=1 \text{sec.}$	$I_{FSM}$	1000	mA
Power Dissipation	$P_D$	350	mW
Operating and Storage Junction Temperature	$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$
Thermal Resistance	$\Theta_{JA}$	357	$^\circ\text{C/W}$

**ELECTRICAL CHARACTERISTICS PER DIODE** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

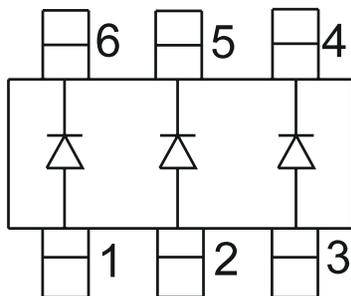
<b>SYMBOL</b>	<b>TEST CONDITIONS</b>	<b>MIN</b>	<b>MAX</b>	<b>UNITS</b>
$I_R$	$V_R=20\text{V}$		25	nA
$BV_R$	$I_R=5.0\mu\text{A}$	75		V
$BV_R$	$I_R=100\mu\text{A}$	100		V
$V_F$	$I_F=100\text{mA}$		1.0	V
$C_T$	$V_R=0, f=1 \text{MHz}$		4.0	pF
$t_{rr}$	$I_R=I_F=10\text{mA}, R_L=100\Omega \text{ Rec. to } 1.0\text{mA}$		4.0	ns

**MECHANICAL OUTLINE - SOT-26 CASE**



**All Dimensions in Inches (mm)**

**Pin Configuration**



**Lead Code**

- 1) Anode 1
- 2) Anode 2
- 3) Anode 3
- 4) Cathode 3
- 5) Cathode 2
- 6) Cathode 1